

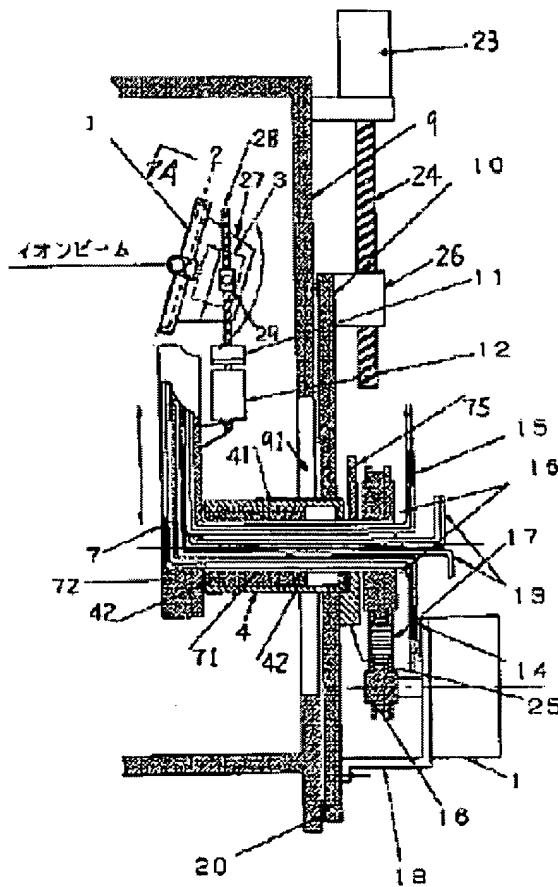
## ION IMPLANTER

**Patent number:** JP11007915  
**Publication date:** 1999-01-12  
**Inventor:** HIDAKA YOSHITOMO; OKADA KEIJI  
**Applicant:** SUMITOMO EATON NOBA KK  
**Classification:**  
 - international: H01J37/317; H01L21/265  
 - european:  
**Application number:** JP19970158617 19970616  
**Priority number(s):**

### Abstract of JP11007915

**PROBLEM TO BE SOLVED:** To provide an ion implanter of a sheet capable of uniformly implanting ions to a semiconductor wafer with an emitting direction of an ion beam fixed.

**SOLUTION:** An emitting direction of an ion beam is fixed. Ions are implanted to a semiconductor wafer 1 while the semiconductor wafer 1 is mechanically moved laterally and vertically. For this purpose, an oscillating mechanism is provided for reciprocally and laterally moving a wafer platen 2, which holds the semiconductor wafer 1 therein, at a constant speed inside a vacuum container 9, and a vertically driving mechanism is provided for vertically moving the wafer platen 2 at another constant speed.



Data supplied from the esp@cenet database - Patent Abstracts of Japan

BEST AVAILABLE COPY